

TLV2172-Q1 36-V, Single-Supply, Low-Power Operational Amplifier for Cost-Sensitive Systems

1 Features

- Qualified for Automotive Applications
- AEC-Q100 Qualified With the Following Results:
 - Device Temperature Grade 1: -40°C to $+125^{\circ}\text{C}$ Ambient Operating Temperature Range
 - Device HBM ESD Classification Level 3A
 - Device CDM ESD Classification Level C6
- Supply Range: 4.5 V to 36 V, ± 2.25 V to ± 18 V
- Low Noise: $9\text{ nV}/\sqrt{\text{Hz}}$
- Low Offset Drift: $\pm 1\text{ }\mu\text{V}/^{\circ}\text{C}$ (Typical)
- EMI-Hardened
- Input Range Includes Negative Supply
- Rail-to-Rail Output
- Gain Bandwidth: 10 MHz
- Slew Rate: $10\text{ V}/\mu\text{s}$
- Low Quiescent Current: 1.6 mA per Amplifier
- High Common-Mode Rejection: 116 dB (Typical)
- Low Input Bias Current: 10 pA

2 Applications

- Automotive
- HEV and EV Power Trains
- Advanced Driver Assist (ADAS)
- Automotive Climate Controls
- Avionics and Landing Gear
- Medical Instrumentation
- Current Sensing

3 Description

The TLV2172-Q1 operational amplifier features a THD+N of 0.0002% at 1 kHz with the ability to operate on supplies ranging from 4.5 V (± 2.25 V) to 36 V (± 18 V). These features, along with low noise and very high PSRR, enable the TLV2172-Q1 to amplify microvolt-level signals in applications such as HEV and EV automobiles and power trains, medical instrumentation, and more. The TLV2172-Q1 device offers good offset and drift, a high bandwidth of 10 MHz, and a slew rate of $10\text{ V}/\mu\text{s}$ with only 2.3 mA of quiescent current over temperature (maximum.)

Unlike most op amps that are specified at only one supply voltage, the TLV2172-Q1 device is specified from 4.5 V to 36 V. Input signals beyond the supply rails do not cause phase reversal. The TLV2172-Q1 device is stable with capacitive loads up to 300 pF. The input can operate 100 mV below the negative rail and within 2 V of the positive rail for normal operation. Note that the device can operate with a full rail-to-rail input 100 mV beyond the positive rail, but with reduced performance within 2 V of the positive rail.

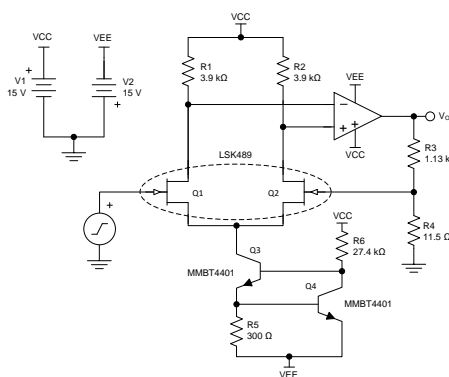
The TLV2172-Q1 op amp is specified from -40°C to $+125^{\circ}\text{C}$.

Device Information⁽¹⁾

PART NUMBER	PACKAGE	BODY SIZE (NOM)
TLV2172-Q1	VSSOP (8)	3.00 mm x 3.00 mm

(1) For all available packages, see the orderable addendum at the end of the data sheet.

Simplified Schematic



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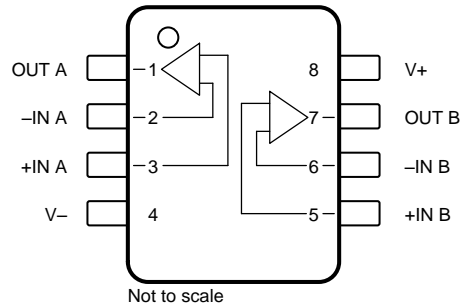
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4 Revision History

DATE	REVISION	NOTES
December 2017	*	Initial release.

5 Pin Configuration and Functions

**D and DGK Packages
8-Pin SOIC and VSSOP
Top View**



Not to scale

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
-IN A	2	I	Inverting input, channel A
-IN B	6	I	Inverting input, channel B
+IN A	3	I	Noninverting input, channel A
+IN B	5	I	Noninverting input, channel B
OUT A	1	O	Output, channel A
OUT B	7	O	Output, channel B
V-	4	—	Negative (lowest) power supply
V+	8	—	Positive (highest) power supply

6 Specifications

6.1 Absolute Maximum Ratings

 over operating free-air temperature range (unless otherwise noted)⁽¹⁾

		MIN	MAX	UNIT	
Voltage	Supply voltage, V+ to V-	-20	20	V	
	Single-supply voltage		40		
	Signal input pin ⁽²⁾	Common-mode	(V-) - 0.5		(V+) + 0.5
		Differential ⁽³⁾	-0.5		0.5
Current	Signal input pin	-10	10	mA	
	Output short-circuit ⁽⁴⁾	Continuous			
Operating, T _A		-55	150	°C	
Junction, T _J			150		
Storage, T _{stg}		-65	150		

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) Transient conditions that exceed these voltage ratings must be current limited to 10 mA or less.

(3) See the *Electrical Overstress* section for more information.

(4) Short-circuit to ground, one amplifier per package.

6.2 ESD Ratings

		VALUE	UNIT
V _(ESD)	Electrostatic discharge	Human-body model (HBM), per AEC Q100-002 ⁽¹⁾	±4000
		Charged-device model (CDM), per AEC Q100-011	±1000

(1) AEC Q100-002 indicates that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
Supply voltage, (V+) - (V-)	Single-supply	4.5		36	V
	Dual-supply	±2.25		±18	
Specified temperature		-40		125	°C

6.4 Thermal Information: TLV2172-Q1

THERMAL METRIC ⁽¹⁾		TLV2172-Q1		UNIT
		D (SOIC)	DGK (VSSOP)	
		8 PINS	8 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	116.1	158	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	69.8	48.6	°C/W
R _{θJB}	Junction-to-board thermal resistance	56.6	78.7	°C/W
ψ _{JT}	Junction-to-top characterization parameter	22.5	3.9	°C/W
ψ _{JB}	Junction-to-board characterization parameter	56.1	77.3	°C/W
R _{θJC(bot)}	Junction-to-case (bottom) thermal resistance	—	—	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application report.

6.5 Electrical Characteristics

at $T_A = 25^\circ\text{C}$, $V_S = \pm 2.25\text{ V}$ to $\pm 18\text{ V}$, $V_{CM} = V_{OUT} = V_S / 2$, and $R_L = 10\text{ k}\Omega$ connected to $V_S / 2$ (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFFSET VOLTAGE						
V_{OS}	Input offset voltage	$T_A = 25^\circ\text{C}$		0.5	1.7	mV
		$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$			2	
dV_{OS}/dT	Input offset voltage drift	$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		1		$\mu\text{V}/^\circ\text{C}$
PSRR	Power-supply rejection ratio	$V_S = 4\text{ V}$ to 36 V , $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	100	120		dB
	Channel separation, DC			5		$\mu\text{V}/\text{V}$
INPUT BIAS CURRENT						
I_B	Input bias current	$T_A = 25^\circ\text{C}$		± 10		pA
I_{OS}	Input offset current	$T_A = 25^\circ\text{C}$		± 2		pA
NOISE						
	Input voltage noise	$f = 0.1\text{ Hz}$ to 10 Hz		2.5		μV_{PP}
e_n	Input voltage noise density	$f = 100\text{ Hz}$		14		$\text{nV}/\sqrt{\text{Hz}}$
		$f = 1\text{ kHz}$		9		$\text{nV}/\sqrt{\text{Hz}}$
i_n	Input current noise density	$f = 1\text{ kHz}$		1.6		$\text{fA}/\sqrt{\text{Hz}}$
INPUT VOLTAGE						
V_{CM}	Common-mode voltage range ⁽¹⁾		$(V_-) - 0.1$		$(V_+) - 2$	V
CMRR	Common-mode rejection ratio	$V_S = \pm 18\text{ V}$, $(V_-) - 0.1\text{ V} < V_{CM} < (V_+) - 2\text{ V}$ $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	94	116		dB
INPUT IMPEDANCE						
	Differential			$100 \parallel 4$		$\text{M}\Omega \parallel \text{pF}$
	Common-mode			$6 \parallel 4$		$10^{13}\ \Omega \parallel \text{pF}$
OPEN-LOOP GAIN						
A_{OL}	Open-loop voltage gain	$(V_-) + 0.35\text{ V} < V_O < (V_+) - 0.35\text{ V}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	97	115		dB
		$(V_-) + 0.5\text{ V} < V_O < (V_+) - 0.5\text{ V}$, $R_L = 2\text{ k}\Omega$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		107		
FREQUENCY RESPONSE						
GBP	Gain bandwidth product			10		MHz
SR	Slew rate	$G = +1$		10		$\text{V}/\mu\text{s}$
t_s	Settling time	To 0.1%, $V_S = \pm 18\text{ V}$, $G = 1$, 10-V step		2		μs
		To 0.01% (12-bit), $V_S = \pm 18\text{ V}$, $G = +1$, 10-V step			3.2	
	Overload recovery time	$V_{IN} \times \text{gain} > V_S$		200		ns
THD+N	Total harmonic distortion + noise	$V_S = 36\text{ V}$, $G = +1$, $f = 1\text{ kHz}$, $V_O = 3.5\text{ V}_{RMS}$		0.0002%		
OUTPUT						
V_O	Voltage output swing from rail	$V_S = \pm 18\text{ V}$, $R_L = 10\text{ k}\Omega$	$T_A = 25^\circ\text{C}$	70		mV
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	95		
		$V_S = \pm 18\text{ V}$, $R_L = 2\text{ k}\Omega$	$T_A = 25^\circ\text{C}$	330	400	
			$T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$	470	530	
I_{SC}	Short-circuit current			± 75		mA
C_{LOAD}	Capacitive load drive			See Typical Characteristics		pF
R_O	Open-loop output resistance	$f = 1\text{ MHz}$, $I_O = 0\text{ A}$		60		Ω
POWER SUPPLY						
V_S	Specified voltage range		4.5		36	V
I_Q	Quiescent current per amplifier	$I_O = 0\text{ A}$, $T_A = -40^\circ\text{C}$ to $+125^\circ\text{C}$		1.6	2.3	mA

(1) The input range can be extended beyond $(V_+) - 2\text{ V}$ up to V_+ . See the [Typical Characteristics](#) and [Application and Implementation](#) sections for additional information.

6.6 Typical Characteristics

at $V_S = \pm 18\text{ V}$, $V_{CM} = V_S / 2$, $R_{LOAD} = 10\text{ k}\Omega$ connected to $V_S / 2$, and $C_L = 100\text{ pF}$ (unless otherwise noted)

Table 1. Characteristic Performance Measurements

DESCRIPTION	FIGURE
Offset Voltage Production Distribution	Figure 1
Offset Voltage vs Common-Mode Voltage	Figure 2
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Quiescent Current vs Supply Voltage	Figure 9
Open-Loop Gain and Phase vs Frequency	Figure 10
Closed-Loop Gain vs Frequency	Figure 11
Open-Loop Output Impedance vs Frequency	Figure 12
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Small-Signal Step Response (10 mV)	Figure 16 , Figure 17
Large-Signal Step Response	Figure 18 , Figure 19
Large-Signal Settling Time	Figure 20 , Figure 21
Short-Circuit Current vs Temperature	Figure 22
Maximum Output Voltage vs Frequency	Figure 23
EMIRR IN+ vs Frequency	Figure 24

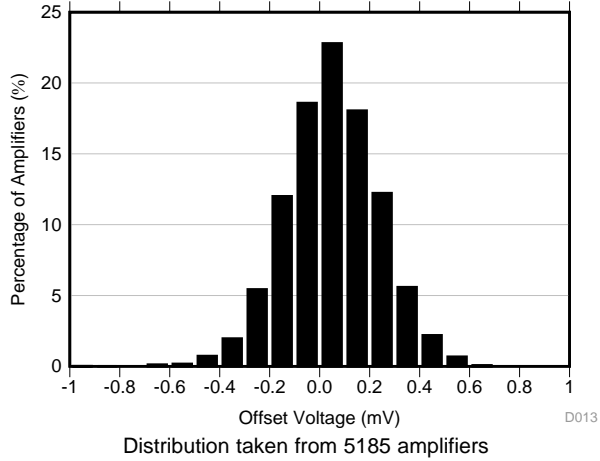


Figure 1. Offset Voltage Production Distribution Histogram

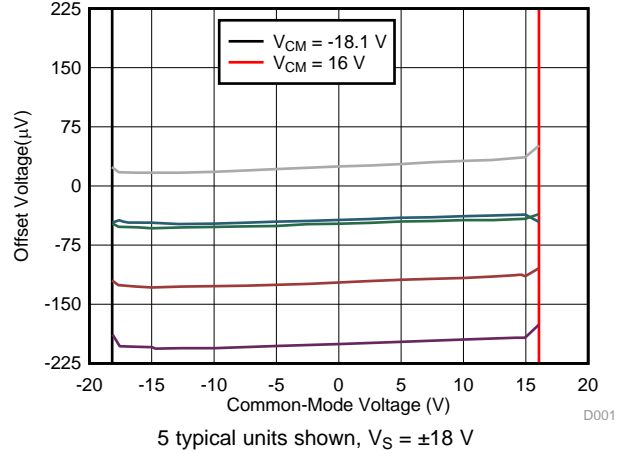


Figure 2. Offset Voltage vs Common-Mode Voltage

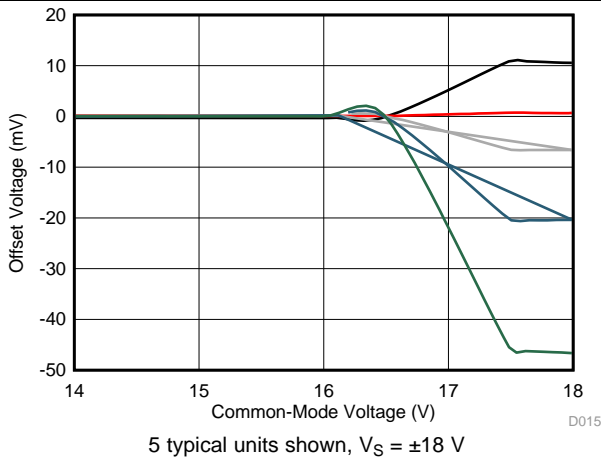


Figure 3. Offset Voltage vs Common-Mode Voltage (Upper Stage)

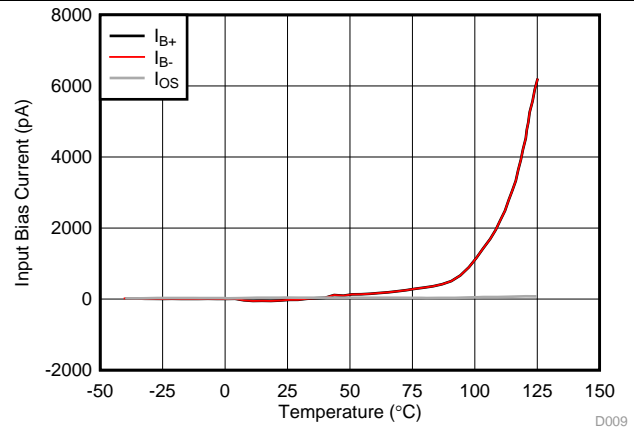


Figure 4. Input Bias Current vs Temperature

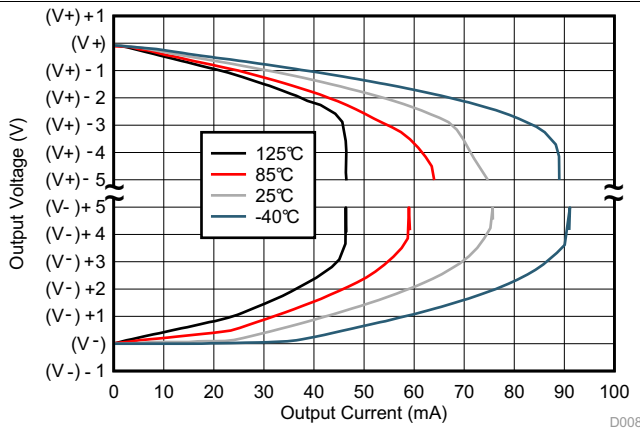


Figure 5. Output Voltage Swing vs Output Current (Maximum Supply)

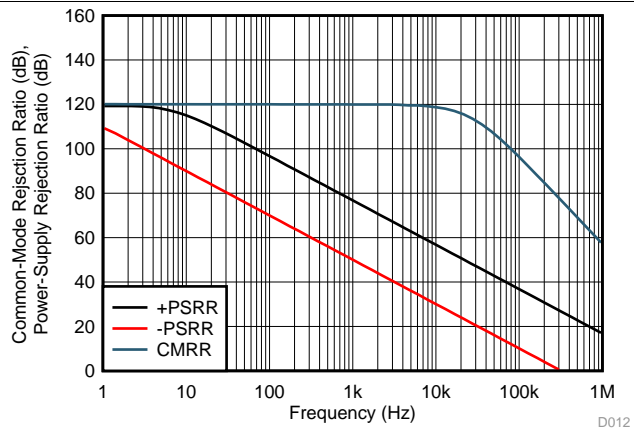


Figure 6. CMRR and PSRR vs Frequency (Referred-to-Input)

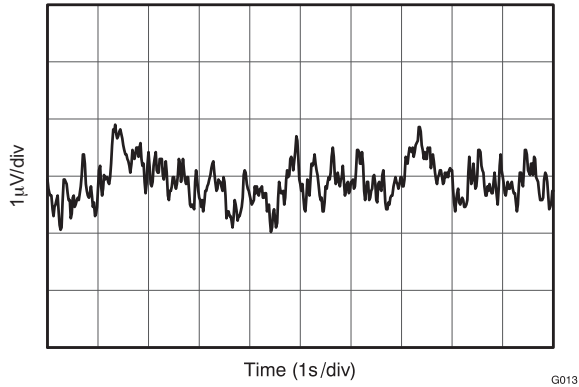


Figure 7. 0.1-Hz to 10-Hz Noise

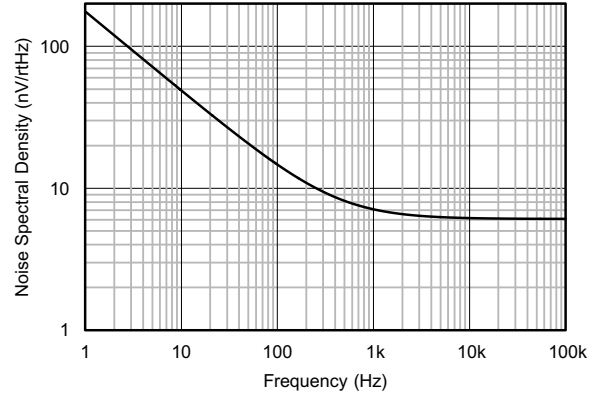


Figure 8. Input Voltage Noise Spectral Density vs Frequency

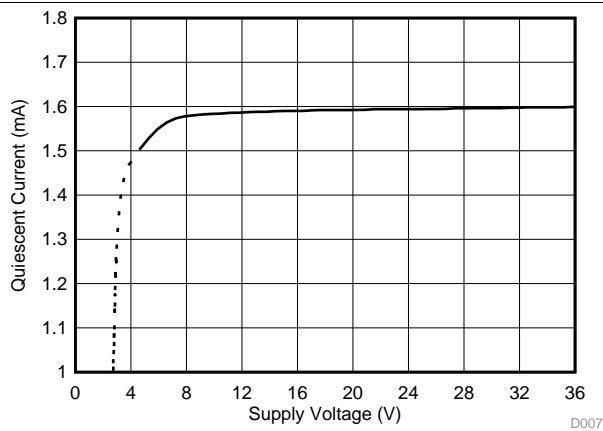


Figure 9. Quiescent Current vs Supply Voltage

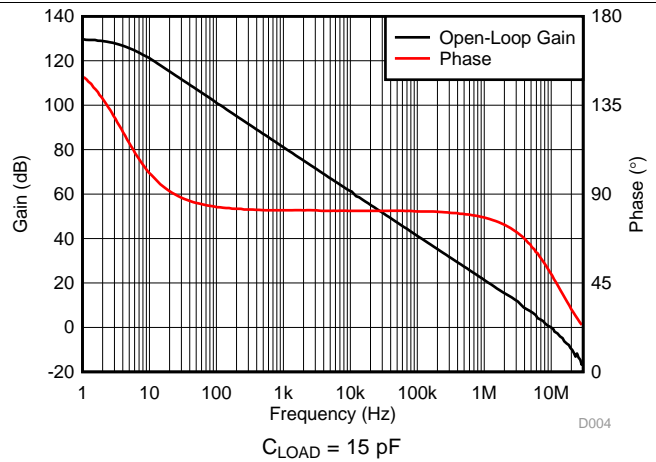


Figure 10. Open-Loop Gain and Phase vs Frequency

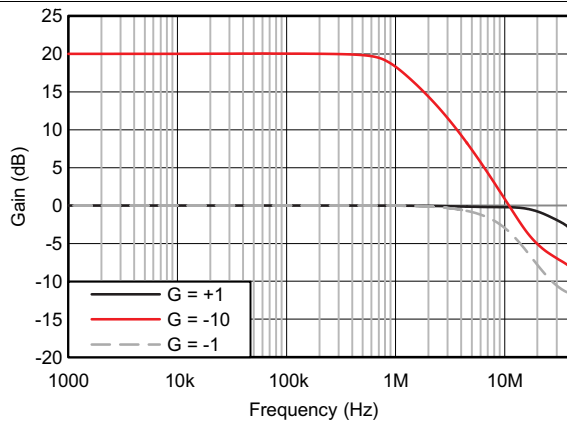


Figure 11. Closed-Loop Gain vs Frequency

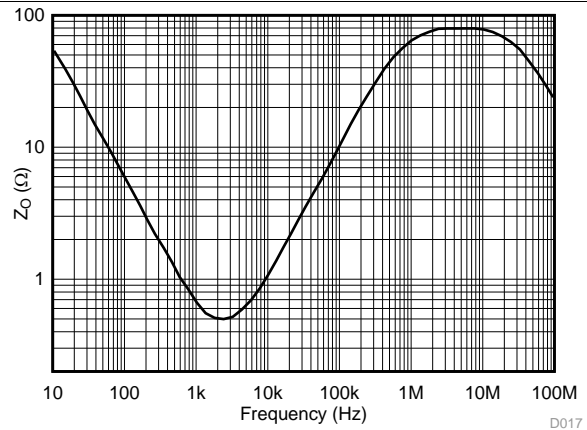


Figure 12. Open-Loop Output Impedance vs Frequency

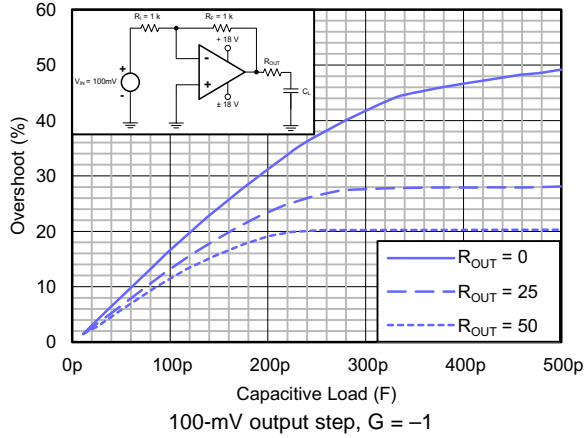


Figure 13. Small-Signal Overshoot vs Capacitive Load

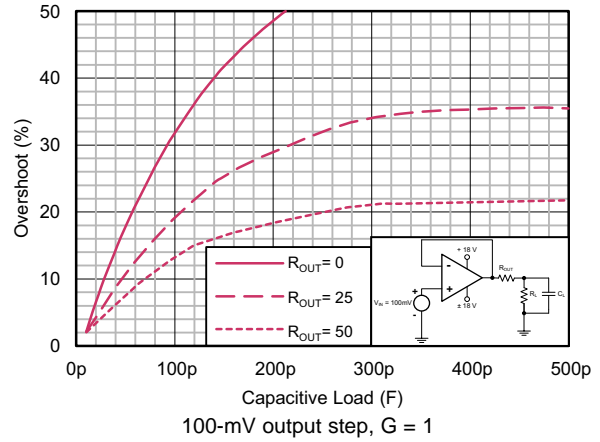


Figure 14. Small-Signal Overshoot vs Capacitive Load

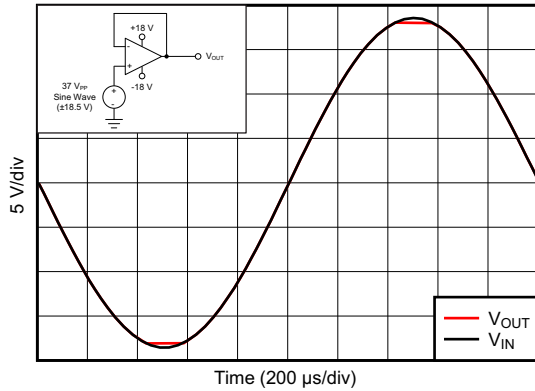


Figure 15. No Phase Reversal

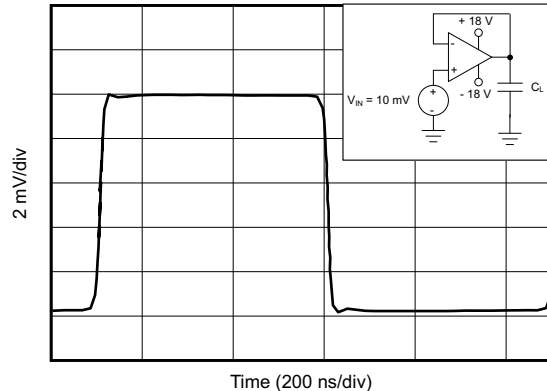


Figure 16. Small-Signal Step Response

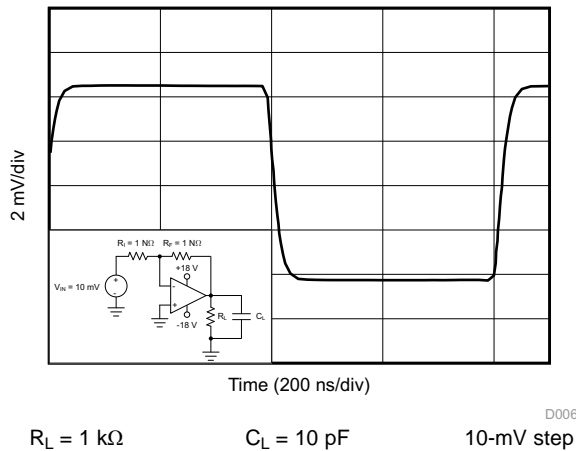


Figure 17. Small-Signal Step Response

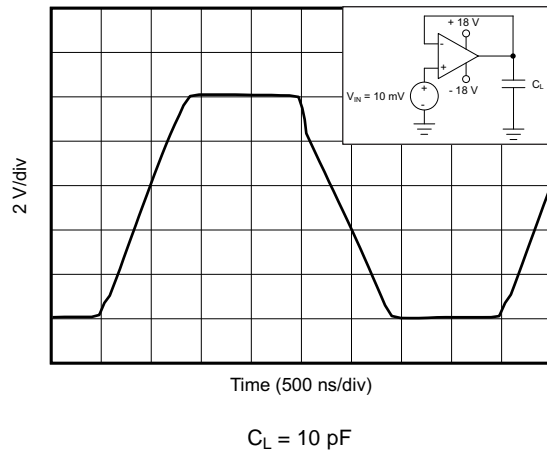
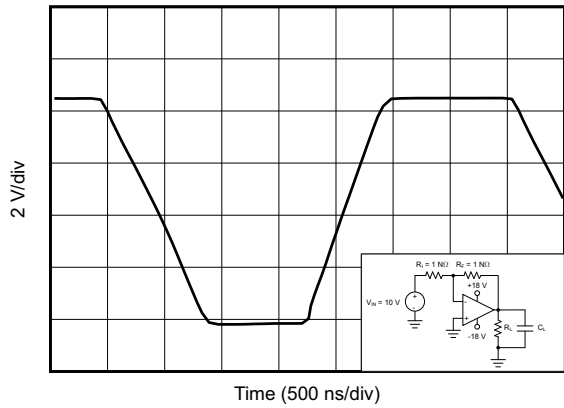


Figure 18. Large-Signal Step Response

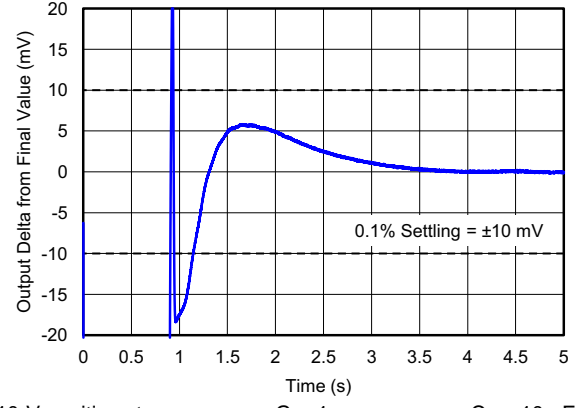


$R_L = 1\text{ k}\Omega$

$C_L = 10\text{ pF}$

D005

Figure 19. Large-Signal Step Response

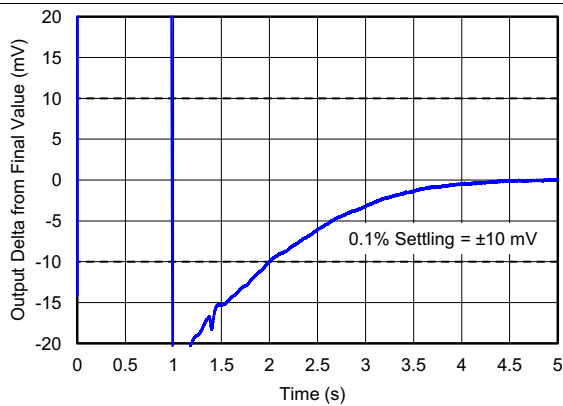


10-V positive step

$G = 1$

$C_L = 10\text{ pF}$

Figure 20. Large-Signal Settling Time



10-V negative step

$G = 1$

$C_L = 10\text{ pF}$

Figure 21. Large-Signal Settling Time

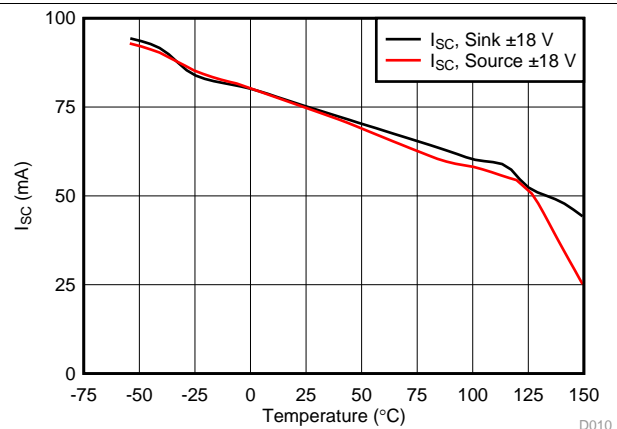


Figure 22. Short-Circuit Current vs Temperature

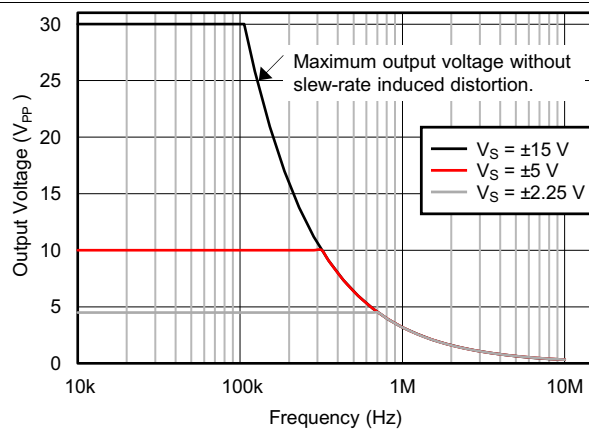
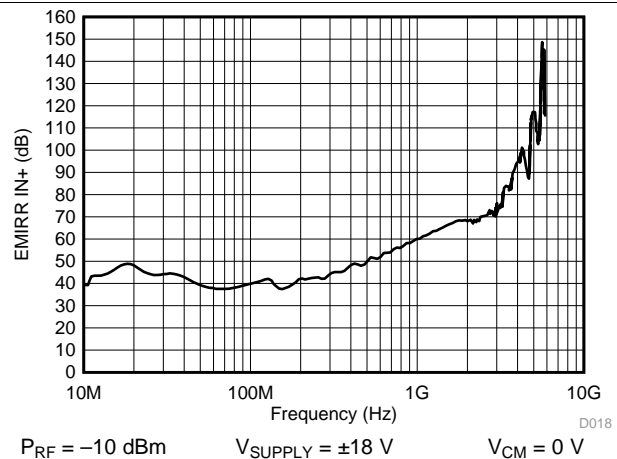


Figure 23. Maximum Output Voltage vs Frequency



$P_{RF} = -10\text{ dBm}$

$V_{SUPPLY} = \pm 18\text{ V}$

$V_{CM} = 0\text{ V}$

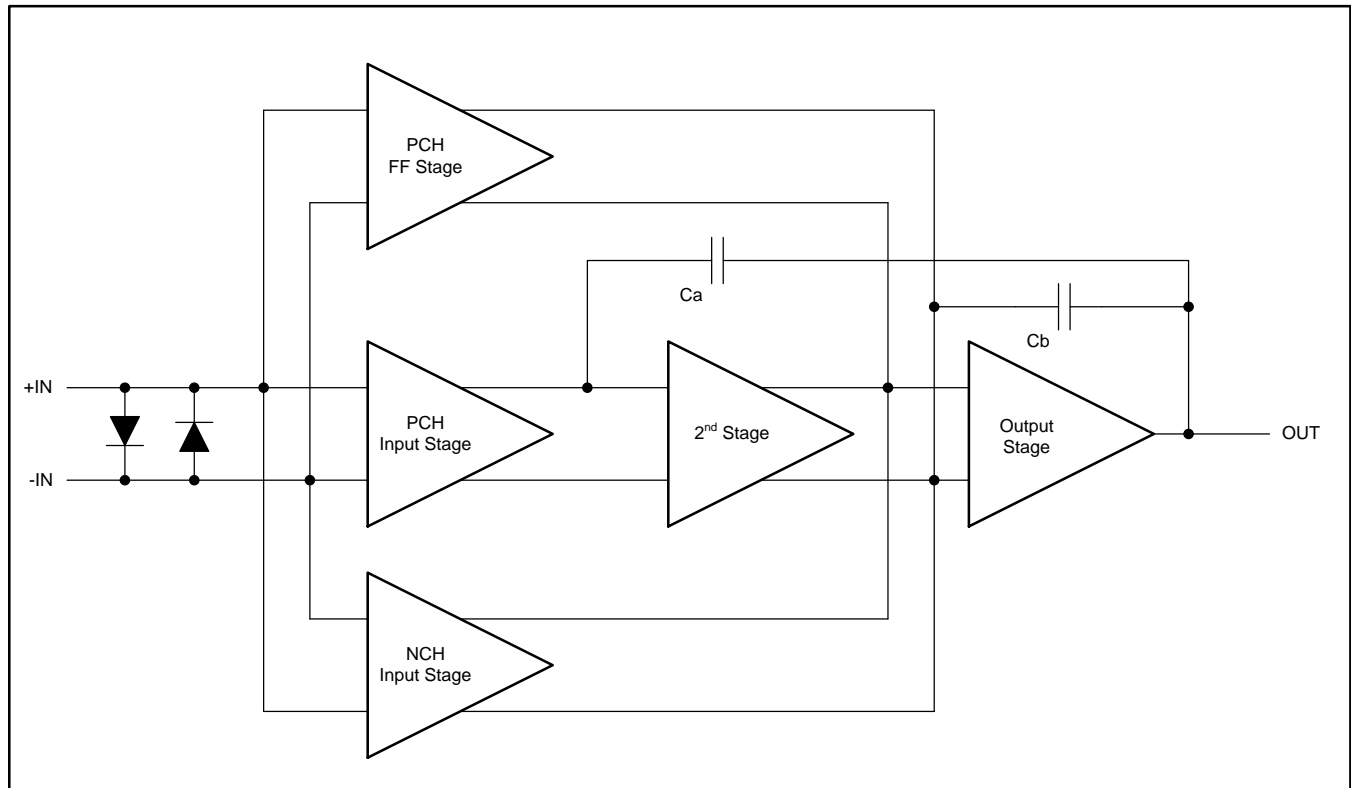
Figure 24. EMIRR IN+ vs Frequency

7 Detailed Description

7.1 Overview

The TLV2172-Q1 operational amplifier provides high overall performance, making these devices designed for many general-purpose applications. The excellent offset drift of only $1 \mu\text{V}/^\circ\text{C}$ provides excellent stability over the entire temperature range. In addition, the device offers very good overall performance with high CMRR, PSRR, and A_{OL} .

7.2 Functional Block Diagram



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7.3 Feature Description

7.3.1 Operating Characteristics

The TLV2172-Q1 amplifier is specified for operation from 4.5 V to 36 V (± 2.25 V to ± 18 V). Many of the specifications apply from -40°C to $+125^{\circ}\text{C}$. Parameters that can exhibit significant variance with regard to operating voltage or temperature are shown in the [Typical Characteristics](#) section.

7.3.2 Phase-Reversal Protection

The TLV2172-Q1 device has an internal phase-reversal protection. Many operational amplifiers exhibit a phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in noninverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The input of the TLV2172-Q1 prevents phase reversal with excessive common-mode voltage. Instead, the output limits into the appropriate rail. This performance is shown in [Figure 25](#).

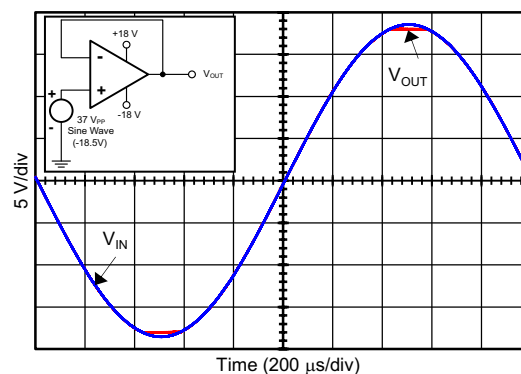


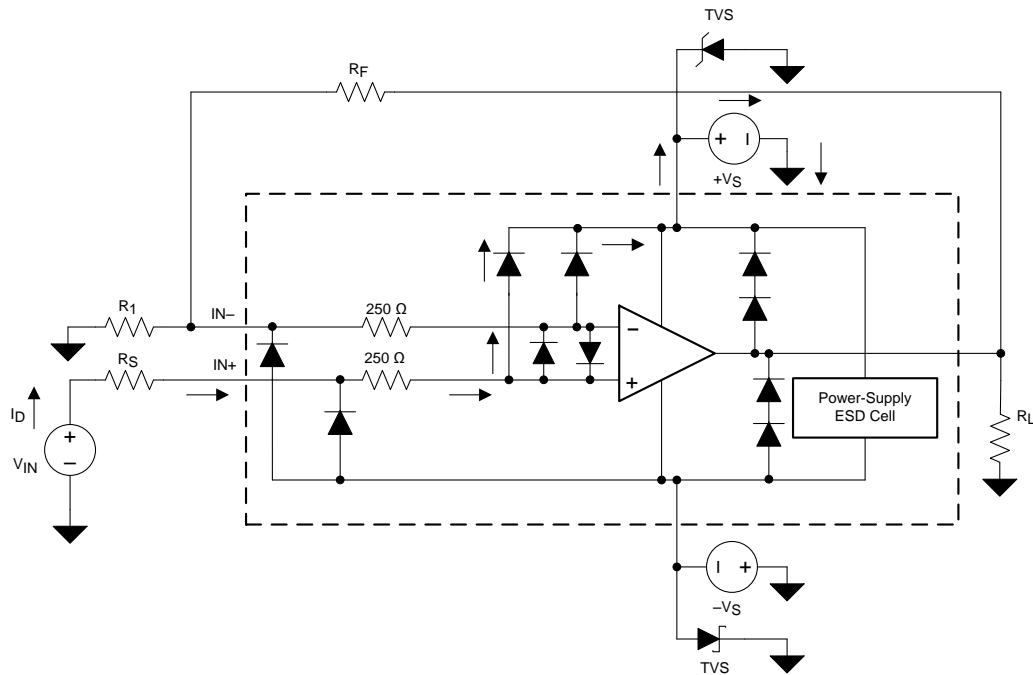
Figure 25. No Phase Reversal

7.3.3 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress. These questions tend to focus on the device inputs, but can involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits for protection from accidental ESD events both before and during product assembly.

A good understanding of this basic ESD circuitry and the relevance to an electrical overstress event is helpful. [Figure 26](#) shows the ESD circuits contained in the TLV2172-Q1 (indicated by the dashed box). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where the diodes meet at an absorption device internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

Feature Description (continued)



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Figure 26. Equivalent Internal ESD Circuitry Relative to a Typical Circuit Application

An ESD event produces a short-duration, high-voltage pulse that is transformed into a short-duration, high-current pulse when discharging through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent damage. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more amplifier device pins, current flows through one or more steering diodes. Depending on the path that the current takes, the absorption device can activate. The absorption device has a trigger, or threshold voltage, that is above the normal operating voltage of the TLV2172-Q1 but below the device breakdown voltage level. When this threshold is exceeded, the absorption device quickly activates and clamps the voltage across the supply rails to a safe level.

When the operational amplifier connects into a circuit, as shown in Figure 26, the ESD protection components are intended to remain inactive and do not become involved in the application circuit operation. However, circumstances can arise where an applied voltage exceeds the operating voltage range of a given pin. If this condition occurs, there is a risk that some internal ESD protection circuits can turn on and conduct current. Any such current flow occurs through steering-diode paths and rarely involves the absorption device.

Figure 26 shows a specific example where the input voltage (V_{IN}) exceeds the positive supply voltage ($V+$) by 500 mV or more. Much of what happens in the circuit depends on the supply characteristics. If $V+$ can sink the current, then one of the upper input steering diodes conducts and directs current to $V+$. Excessively high current levels can flow with increasingly higher V_{IN} . As a result, the data sheet specifications recommend that applications limit the input current to 10 mA.

If the supply is not capable of sinking the current, V_{IN} can begin sourcing current to the operational amplifier and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings.

Feature Description (continued)

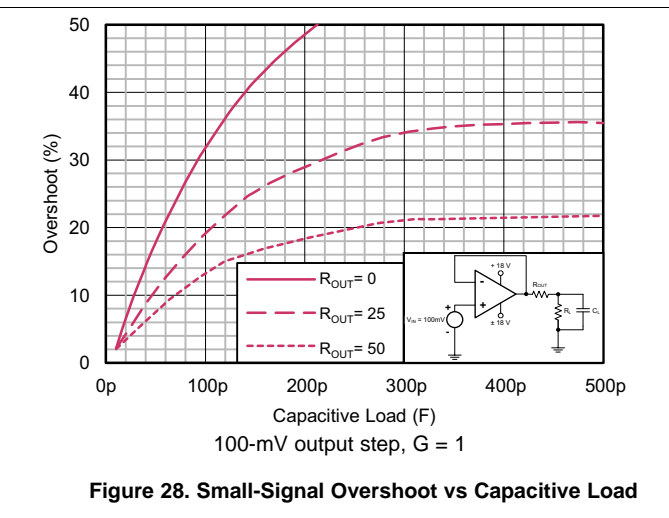
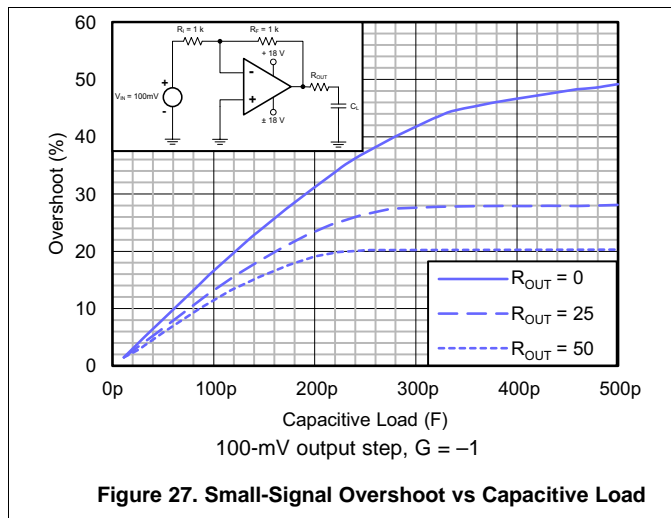
Another common question involves what happens to the amplifier if an input signal is applied to the input when the power supplies ($V+$ or $V-$) are at 0 V. Again, this question depends on the supply characteristic when at 0 V, or at a level below the input signal amplitude. If the supplies appear as high impedance, then the input source supplies the operational amplifier current through the current-steering diodes. This state is not a normal bias condition; most likely, the amplifier does not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current and any resistance in the input path.

If there is any uncertainty about the ability of the supply to absorb this current, add external Zener diodes to the supply pins; see [Figure 26](#). Select the Zener voltage so that the diode does not turn on during normal operation. However, the Zener voltage must be low enough so that the Zener diode conducts if the supply pin begins to rise above the safe-operating, supply-voltage level.

The input pins of the TLV2172-Q1 are protected from excessive differential voltage with back-to-back diodes; see [Figure 26](#). In most circuit applications, the input protection circuitry has no effect. However, in low-gain or $G = 1$ circuits, fast-ramping input signals can forward-bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. If the input signal is fast enough to create this forward-bias condition, then limit the input signal current to 10 mA or less. If the input signal current is not inherently limited, an input series resistor can limit the input signal current. This input series resistor degrades the low-noise performance of the TLV2172-Q1. [Figure 26](#) shows an example configuration that implements a current-limiting feedback resistor.

7.3.4 Capacitive Load and Stability

The dynamic characteristics of the TLV2172-Q1 are optimized for common operating conditions. The combination of low closed-loop gain and high capacitive loads decreases the phase margin of the amplifier and can lead to gain peaking or oscillations. As a result, heavier capacitive loads must be isolated from the output. The simplest way to achieve this isolation is to add a small resistor (for example, R_{OUT} equal to 50 Ω) in series with the output. [Figure 27](#) and [Figure 28](#) show graphs of small-signal overshoot versus capacitive load for several values of R_{OUT} . See the [Feedback Plots Define Op Amp AC Performance](#) application note for details of analysis techniques and application circuits.



7.4 Device Functional Modes

7.4.1 Common-Mode Voltage Range

The input common-mode voltage range of the TLV2172-Q1 device extends 100 mV below the negative rail and within 2 V of the top rail for normal operation.

This device can operate with full rail-to-rail input 100 mV beyond the top rail, but with reduced performance within 2 V of the top rail. [Table 2](#) lists the typical performances in this range.

Table 2. Typical Performance for Common-Mode Voltages Within 2 V of the Positive Supply

PARAMETER	MIN	TYP	MAX	UNIT
Input common-mode voltage	$(V+) - 2$		$(V+) + 0.1$	V
Offset voltage		7		mV
Offset voltage vs temperature		12		$\mu\text{V}/^\circ\text{C}$
Common-mode rejection		65		dB
Open-loop gain		60		dB
Gain-bandwidth product		0.3		MHz
Slew rate		0.3		$\text{V}/\mu\text{s}$

7.4.2 Overload Recovery

Overload recovery is defined as the time required for the operational amplifier output to recover from the saturated state to the linear state. The output devices of the operational amplifier enter the saturation region when the output voltage exceeds the rated operating voltage, which is a result from the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return back to the normal state. After the charge carriers return back to the equilibrium state, the device begins to slew at the normal slew rate. As a result, the propagation delay in case of an overload condition is the sum of the overload recovery time and the slew time. The overload recovery time for the TLV2172-Q1 is approximately 2 μs .

8 Application and Implementation

NOTE

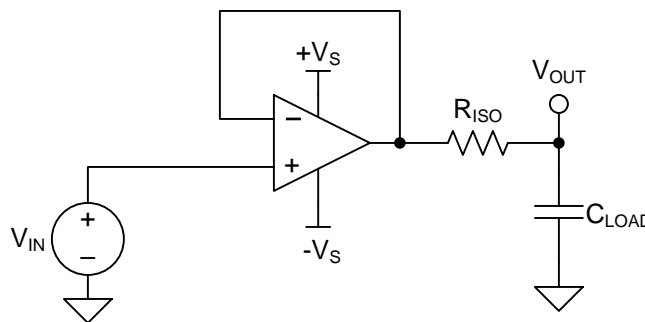
Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

The TLV2172-Q1 operational amplifier provides high overall performance in a large number of general-purpose applications. As with all amplifiers, applications with noisy or high-impedance power supplies require decoupling capacitors placed close to the device pins. In most cases, 0.1- μ F capacitors are adequate. Follow the additional recommendations in the [Layout Guidelines](#) section to achieve the maximum performance from this device. Many applications introduce capacitive loading to the output of the amplifier (which potentially causes instability). To stabilize the amplifier, add an isolation resistor between the amplifier output and the capacitive load. [Typical Application](#) section shows the process for selecting a resistor.

8.2 Typical Application

This circuit can drive capacitive loads (such as cable shields, reference buffers, MOSFET gates, and diodes). The circuit uses an isolation resistor (R_{ISO}) to stabilize the output of an operational amplifier. R_{ISO} modifies the open-loop gain of the system to ensure that the circuit has sufficient phase margin.



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Figure 29. Unity-Gain Buffer With R_{ISO} Stability Compensation

8.2.1 Design Requirements

The design requirements are:

- Supply voltage: 30 V (± 15 V)
- Capacitive loads: 100 pF, 1000 pF, 0.01 μ F, 0.1 μ F, and 1 μ F
- Phase margin: 45° and 60°

8.2.2 Detailed Design Procedure

[Figure 29](#) shows a unity-gain buffer driving a capacitive load. [Equation 1](#) shows the transfer function for the circuit in [Figure 29](#). [Figure 29](#) does not show the open-loop output resistance of the operational amplifier (R_o).

$$T(s) = \frac{1 + C_{LOAD} \times R_{ISO} \times s}{1 + (R_o + R_{ISO}) \times C_{LOAD} \times s} \quad (1)$$

The transfer function in [Equation 1](#) has a pole and a zero. The frequency of the pole (f_p) is determined by $(R_o + R_{ISO})$ and C_{LOAD} . The R_{ISO} and C_{LOAD} components determine the frequency of the zero (f_z). A stable system is obtained by selecting R_{ISO} so that the rate of closure (ROC) between the open-loop gain (A_{OL}) and $1/\beta$ is 20 dB per decade. [Figure 30](#) shows the concept. The $1/\beta$ curve for a unity-gain buffer is 0 dB.

Typical Application (continued)

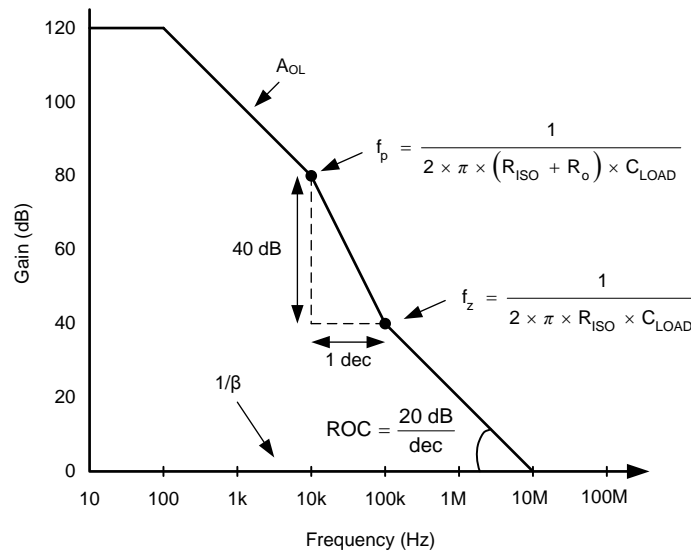


Figure 30. Unity-Gain Amplifier With R_{ISO} Compensation

Typically, ROC stability analysis is simulated. The validity of the analysis depends on multiple factors, especially the accurate modeling of R_o . In addition to simulating the ROC, a robust stability analysis includes a measurement of overshoot percentage and AC gain peaking of the circuit using a function generator, oscilloscope, and gain and phase analyzer. Phase margin is then calculated from these measurements. Table 3 shows the overshoot percentage and AC gain peaking that correspond to phase margins of 45° and 60°. For more details on this design and other alternative devices that can replace the TLV2172-Q1, see the [Capacitive Load Drive Solution Using an Isolation Resistor](#) precision design.

Table 3. Phase Margin versus Overshoot and AC Gain Peaking

PHASE MARGIN	OVERSHOOT	AC GAIN PEAKING
45°	23.3%	2.35 dB
60°	8.8%	0.28 dB

8.2.3 Application Curve

The values of R_{ISO} that yield phase margins of 45° and 60° for various capacitive loads are determined using the described methodology. Figure 31 shows the results.

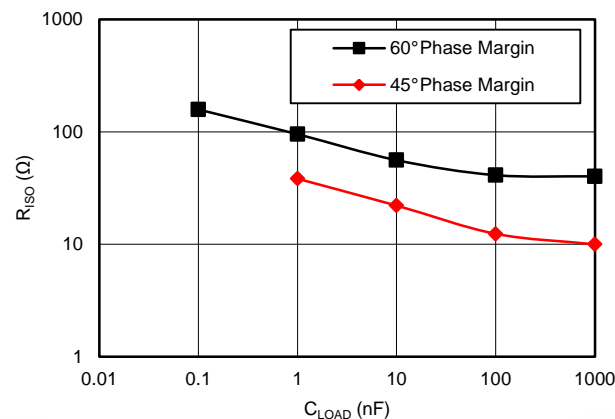


Figure 31. Isolation Resistor Required for Various Capacitive Loads to Achieve a Target Phase Margin

9 Power Supply Recommendations

The TLV2172-Q1 is specified for operation from 4.5 V to 36 V (± 2.25 V to ± 18 V); many specifications apply from -40°C to $+125^{\circ}\text{C}$. Parameters that can exhibit significant variance with regard to operating voltage or temperature are shown in the [Typical Characteristics](#) section.

CAUTION

Supply voltages larger than 40 V can permanently damage the device; see the [Absolute Maximum Ratings](#) table.

Place 0.1- μF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, see the [Layout](#) section.

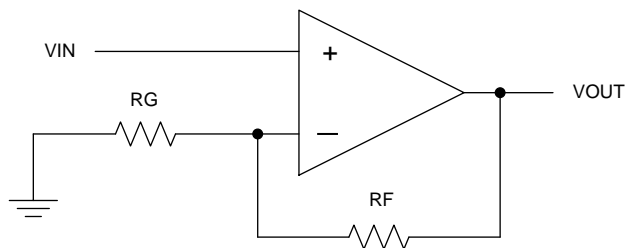
10 Layout

10.1 Layout Guidelines

For best operational performance of the device, use good printed circuit board (PCB) layout practices, including:

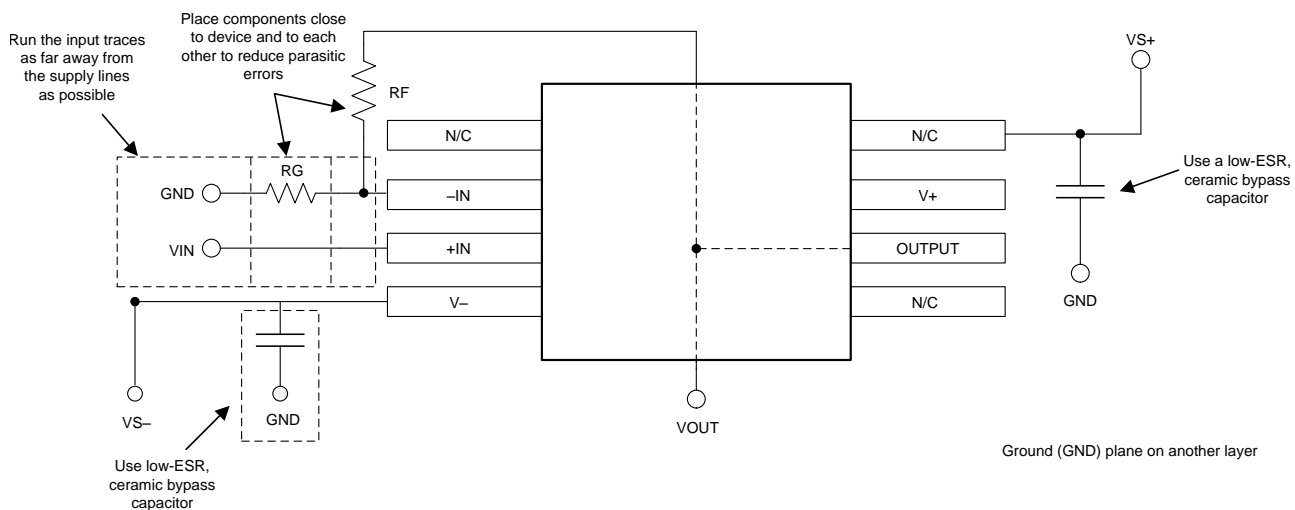
- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and the operational amplifier itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
 - Connect low-ESR, 0.1- μF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of the circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces electromagnetic interference (EMI) noise pickup. Make sure to physically separate digital and analog grounds, paying attention to the flow of the ground current.
- In order to reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicularly is much better than in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in [Figure 33](#), keeping R_F and R_G close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.

10.2 Layout Example



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Figure 32. Schematic Representation



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Figure 33. Operational Amplifier Board Layout for a Noninverting Configuration

11 Device and Documentation Support

11.1 Device Support

11.1.1 Third-Party Products Disclaimer

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11.1.2 Development Support

11.1.2.1 TINA-TI™ (Free Software Download)

TINA-TI™ is a simple, powerful, and easy-to-use circuit simulation program based on a SPICE engine. TINA-TI™ is a free, fully-functional version of the TINA software, preloaded with a library of macromodels in addition to a range of both passive and active models. TINA-TI™ provides all the conventional dc, transient, and frequency domain analysis of SPICE, as well as additional design capabilities.

Available as a [free download](#) from the Analog eLab Design Center, TINA-TI™ offers extensive post-processing capability that allows users to format results in a variety of ways. Virtual instruments offer the ability to select input waveforms and probe circuit nodes, voltages, and waveforms, thus creating a dynamic quick-start tool.

NOTE

These files require that either the TINA software (from DesignSoft™) or the TINA-TI™ software be installed. Download the free TINA-TI™ software from the [TINA-TI™ folder](#).

11.1.2.2 DIP Adapter EVM

The [DIP Adapter EVM](#) tool provides an easy, low-cost way to prototype small surface-mount devices. The evaluation tool uses these TI packages: D or U (SOIC-8), PW (TSSOP-8), DGK (VSSOP-8), DBV (SOT23-6, SOT23-5, and SOT23-3), DCK (SC70-6 and SC70-5), and DRL (SOT563-6). The DIP adapter EVM can also be used with terminal strips or can be wired directly to existing circuits.

11.1.2.3 Universal Op Amp EVM

The [Universal Op Amp EVM](#) is a series of general-purpose, blank circuit boards that simplify prototyping circuits for a variety of device package types. The evaluation module board design allows many different circuits to be constructed easily and quickly. Five models are offered, with each model intended for a specific package type. PDIP, SOIC, VSSOP, TSSOP, and SOT23 packages are all supported.

NOTE

These boards are unpopulated, so users must provide their own devices. TI recommends requesting several op amp device samples when ordering the Universal Op Amp EVM.

11.1.2.4 TI Precision Designs

TI precision designs are analog solutions created by TI's precision analog applications experts and offer the theory of operation, component selection, simulation, a complete PCB schematic and layout, bill of materials, and measured performance of many useful circuits. TI precision designs are available online at www.ti.com/ww/en/analog/precision-designs/.

11.1.2.5 WEBENCH® Filter Designer

The [WEBENCH® Filter Designer](#) is a simple, powerful, and easy-to-use active filter design program. The WEBENCH® Filter Designer allows optimized filter designs to be created by using a selection of TI operational amplifiers and passive components from TI's vendor partners.

Device Support (continued)

Available as a web-based tool from the WEBENCH® design center, the WEBENCH® filter designer allows complete multistage active filter solutions to be designed, optimized, and simulated within minutes.

11.2 Documentation Support

11.2.1 Related Documentation

For related documentation see the following:

- [Feedback Plots Define Op Amp AC Performance](#)
- [EMI Rejection Ratio of Operational Amplifiers](#)
- [Compensate Transimpedance Amplifiers Intuitively](#)
- [Noise Analysis for High-Speed Op Amps](#)

11.3 Related Links

The table below lists quick access links. Categories include technical documents, support and community resources, tools and software, and quick access to order now.

11.4 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. In the upper right corner, click on Alert me to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

11.5 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's [Terms of Use](#).

TI E2E™ Online Community *TI's Engineer-to-Engineer (E2E) Community*. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

11.6 Trademarks

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11.7 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

11.8 Glossary

[SLYZ022](#) — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TLV2172QDQGRQ1	ACTIVE	VSSOP	DGK	8	2500	Green (RoHS & no Sb/Br)	NIPDAUAG	Level-2-260C-1 YEAR	-40 to 125	11Q6	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead/Ball Finish - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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OTHER QUALIFIED VERSIONS OF TLV2172-Q1 :

- Catalog: [TLV2172](#)

NOTE: Qualified Version Definitions:

- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION



QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV2172QDGKRQ1	VSSOP	DGK	8	2500	330.0	12.4	5.3	3.4	1.4	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV2172QDGKRQ1	VSSOP	DGK	8	2500	366.0	364.0	50.0

DGK (S-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 per end.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed 0.50 per side.
 - E. Falls within JEDEC MO-187 variation AA, except interlead flash.



- NOTES:
- A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Publication IPC-7351 is recommended for alternate designs.
 - D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
 - E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

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